

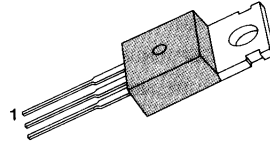
KSD5018**NPN SILICON DARLINGTON TRANSISTOR**

**HIGH VOLTAGE POWER DARLINGTON TR
BUILT-IN RESISTOR BETWEEN BASE AND
EMITTER FOR MOTOR DRIVE**

ABSOLUTE MAXIMUM RATINGS

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}	600	V
Collector Emitter Voltage	V_{CEO}	275	V
Emitter Base Voltage	V_{EBO}	10	V
Collector Current (DC)	I_C	4	A
*Collector Current (Pulse)	I_C	6	A
Base Current (DC)	I_B	0.5	A
Collector Dissipation ($T_C=25^{\circ}\text{C}$)	P_C	40	W
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ 150	$^{\circ}\text{C}$

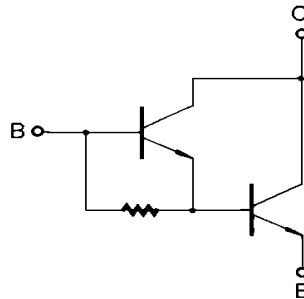
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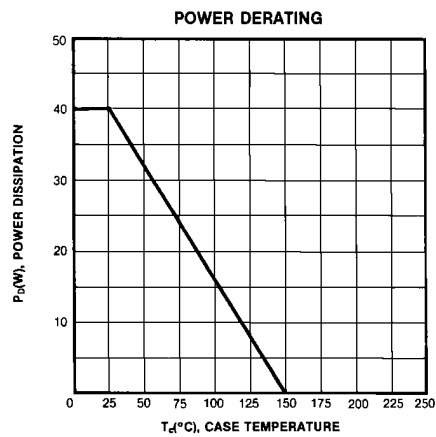
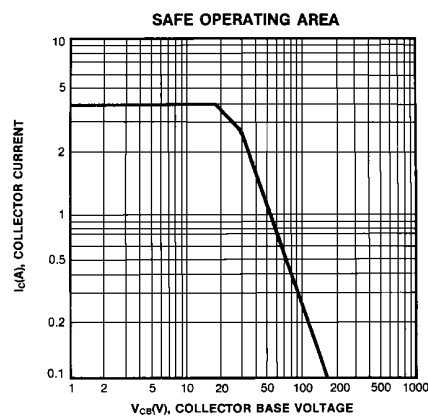
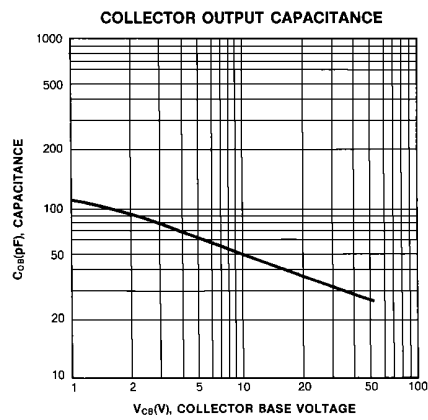
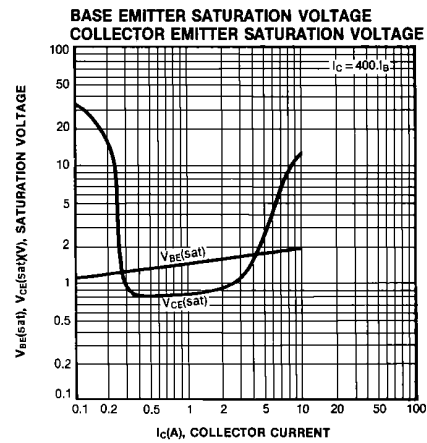
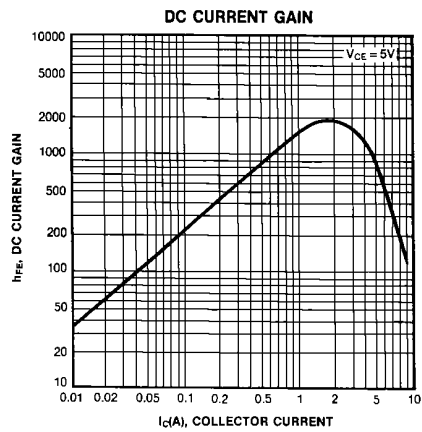


1.Base 2.Collector 3.Emitter

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 1.5\text{A}$, $I_B = 0.05\text{A}$, $L = 25\text{mH}$	275		V
Collector Emitter Voltage	V_{CER}	$I_C = 1\text{mA}$, $R_{BE} = 330\Omega$	600		V
Collector Cutoff Current	I_{CES}	$V_{CE} = 500\text{V}$		1	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 10\text{V}$, $I_C = 0$		1	mA
Collector Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 2\text{A}$, $I_B = 5\text{mA}$		1.5	V
		$I_C = 3\text{A}$, $I_B = 20\text{mA}$		1.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 2\text{A}$, $I_B = 5\text{mA}$		2	V





KSD985/986

NPN EPITAXIAL SILICON
DARLINGTON TRANSISTOR

